

Vladimir Protasenko

List of Publications by Citations

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29
papers

1,430
citations

17
h-index

33
g-index

33
ext. papers

1,632
ext. citations

4.3
avg, IF

4.18
L-index

#	Paper	IF	Citations
29	High-voltage field effect transistors with wide-bandgap EgGa_2O_3 nanomembranes. <i>Applied Physics Letters</i> , 2014 , 104, 203111	3.4	242
28	Esaki Diodes in van der Waals Heterojunctions with Broken-Gap Energy Band Alignment. <i>Nano Letters</i> , 2015 , 15, 5791-8	11.5	237
27	Transistors with chemically synthesized layered semiconductor WS_2 exhibiting 105 room temperature modulation and ambipolar behavior. <i>Applied Physics Letters</i> , 2012 , 101, 013107	3.4	212
26	MBE-grown 232 \times 70 nm deep-UV LEDs using monolayer thin binary GaN/AlN quantum heterostructures. <i>Applied Physics Letters</i> , 2017 , 110, 041108	3.4	85
25	Tunnel-injection quantum dot deep-ultraviolet light-emitting diodes with polarization-induced doping in III-nitride heterostructures. <i>Applied Physics Letters</i> , 2014 , 104, 021105	3.4	68
24	Polarization-engineering in group III-nitride heterostructures: New opportunities for device design. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011 , 208, 1511-1516	1.6	66
23	Layered transition metal dichalcogenides: promising near-lattice-matched substrates for GaN growth. <i>Scientific Reports</i> , 2016 , 6, 23708	4.9	58
22	Tunnel-injection GaN quantum dot ultraviolet light-emitting diodes. <i>Applied Physics Letters</i> , 2013 , 102, 041103	3.4	56
21	N-polar III-nitride quantum well light-emitting diodes with polarization-induced doping. <i>Applied Physics Letters</i> , 2011 , 99, 171104	3.4	55
20	Deep ultraviolet emission from ultra-thin GaN/AlN heterostructures. <i>Applied Physics Letters</i> , 2016 , 109, 241102	3.4	53
19	CdSe nanowires with illumination-enhanced conductivity: Induced dipoles, dielectrophoretic assembly, and field-sensitive emission. <i>Journal of Applied Physics</i> , 2007 , 101, 073704	2.5	48
18	Deep-UV emission at 219 nm from ultrathin MBE GaN/AlN quantum heterostructures. <i>Applied Physics Letters</i> , 2017 , 111, 091104	3.4	42
17	Room temperature microwave oscillations in GaN/AlN resonant tunneling diodes with peak current densities up to 220 kA/cm ² . <i>Applied Physics Letters</i> , 2018 , 112, 103101	3.4	38
16	Two-dimensional electron gases in strained quantum wells for AlN/GaN/AlN double heterostructure field-effect transistors on AlN. <i>Applied Physics Letters</i> , 2014 , 104, 193506	3.4	35
15	Crystal orientation dictated epitaxy of ultrawide-bandgap 5.4- to 8.6-eV $\text{E}(\text{AlGa})\text{O}$ on m-plane sapphire. <i>Science Advances</i> , 2021 , 7,	14.3	35
14	New Tunneling Features in Polar III-Nitride Resonant Tunneling Diodes. <i>Physical Review X</i> , 2017 , 7,	9.1	34
13	Broken Symmetry Effects due to Polarization on Resonant Tunneling Transport in Double-Barrier Nitride Heterostructures. <i>Physical Review Applied</i> , 2019 , 11,	4.3	17

12	Fighting Broken Symmetry with Doping: Toward Polar Resonant Tunneling Diodes with Symmetric Characteristics. <i>Physical Review Applied</i> , 2020 , 13,	4-3	8
11	Phase inclusions as common structural defects in alloyed $\text{Al}_x\text{Ga}_{1-x}\text{O}_3$ and doped AlGaO_3 films. <i>APL Materials</i> , 2021 , 9, 051119	5-7	7
10	Bandgap narrowing and Mott transition in Si-doped $\text{Al}_{0.7}\text{Ga}_{0.3}\text{N}$. <i>Applied Physics Letters</i> , 2019 , 114, 113501	3-4	6
9	Light-emitting diodes with AlN polarization-induced buried tunnel junctions: A second look. <i>Applied Physics Letters</i> , 2020 , 117, 061104	3-4	5
8	MBE growth and donor doping of coherent ultrawide bandgap AlGaIn alloy layers on single-crystal AlN substrates. <i>Applied Physics Letters</i> , 2021 , 118, 092101	3-4	5
7	Self-assembled Ge QDs Formed by High-Temperature Annealing on Al(Ga)As (001). <i>Journal of Electronic Materials</i> , 2015 , 44, 1338-1343	1-9	2
6	Extended Defect Propagation in Highly Tensile-Strained Ge Waveguides. <i>Crystals</i> , 2017 , 7, 157	2-3	2
5	First demonstration of two-dimensional WS_2 transistors exhibiting 105 room temperature modulation and ambipolar behavior 2012 ,		2
4	Bottom tunnel junction blue light-emitting field-effect transistors. <i>Applied Physics Letters</i> , 2020 , 117, 031107	3-4	2
3	Efficient InGaIn p-Contacts for deep-UV Light Emitting Diodes 2019 ,		2
2	Deep-UV LEDs using polarization-induced doping: Electroluminescence at cryogenic temperatures 2015 ,		1
1	Nanomembrane AlGaO_3 high-voltage field effect transistors 2013 ,		1